

Extended Data Figure 8 | Growth of three-junction $MoS_{0.64}Se_{1.36} - WSe_{1.32}S_{0.68}$ lateral alloy heterostructure. a, Optical image of a three-junction $MoS_{2(1-x)}Se_{2x}-WS_{2(1-y)}Se_{2y}$ monolayer lateral heterostructure. b, The corresponding low magnification optical image of the heterostructure shown in a. c, d, Raman (c) and photoluminescence (d) spectra corresponding to the optical image in a between points 1–4. e, Normalized photoluminescence contour

colour plot along the direction perpendicular to the interfaces, as shown in the optical image in the inset. **f**, **g**, Photoluminescence intensity maps at $1.61\,\text{eV}$ (**f**, MoS $_{0.64}$ Se $_{1.36}$ domain) and $1.71\,\text{eV}$ (**g**, WSe $_{1.32}$ So $_{0.68}$ domain) corresponding to the optical image in Fig. 3a. **h–k**, Raman intensity maps (Fig. 3a) at frequency $400.5\,\text{cm}^{-1}$ ($A_{1g(S-Mo)}$ modes, **h**); $264\,\text{cm}^{-1}$ ($A_{1g(S-Mo)}$ modes, **i**); $404\,\text{cm}^{-1}$ ($A_{1g(S-W)}$ mode, **j**); and $256\,\text{cm}^{-1}$ ($A_{1g(Se-W)}$ mode, **k**). Scale bars: **f–k**, $10\,\mu\text{m}$.